

## N- and P-Channel 40-V (D-S) MOSFET

PRODUCT SUMMARY				
	V <sub>DS</sub> (V)	r <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A) <sup>a</sup>	Q <sub>g</sub> (Typ)
N-Channel	40	0.016 at V <sub>GS</sub> = 10 V	8	56
		0.019 at V <sub>GS</sub> = 4.5 V	8	
P-Channel	- 40	0.025 at V <sub>GS</sub> = - 10 V	- 8	6
		0.032 at V <sub>GS</sub> = - 4.5 V	- 7.5	

### FEATURES

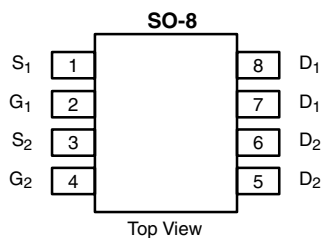
- TrenchFET<sup>®</sup> Power MOSFET
- 100 % R<sub>g</sub> Tested

### APPLICATIONS

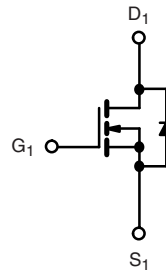
- CCFL Inverter



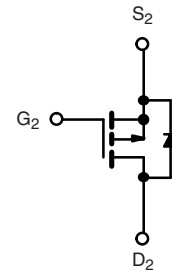
**RoHS**  
COMPLIANT



Ordering Information: Si4563DY-T1-E3 (Lead (Pb)-free)



N-Channel MOSFET



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T <sub>A</sub> = 25 °C, unless otherwise noted					
Parameter	Symbol	N-Channel	P-Channel	Unit	
Drain-Source Voltage	V <sub>DS</sub>	40	- 40	V	
Gate-Source Voltage	V <sub>GS</sub>	± 16			
Continuous Drain Current (T <sub>J</sub> = 150 °C)	I <sub>D</sub>	T <sub>C</sub> = 25 °C	8	- 8	A
		T <sub>C</sub> = 70 °C	8	- 6.5	
		T <sub>A</sub> = 25 °C	8 <sup>b, c</sup>	- 6.6 <sup>b, c</sup>	
		T <sub>A</sub> = 70 °C	6.5 <sup>b, c</sup>	- 5.2 <sup>b, c</sup>	
Pulsed Drain Current (10 μs Pulse Width)	I <sub>DM</sub>	20	- 20	A	
Source-Drain Current Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	2.7		- 2.7
		T <sub>A</sub> = 25 °C	1.6 <sup>b, c</sup>		- 1.6 <sup>b, c</sup>
Pulsed Source-Drain Current	I <sub>SM</sub>	20	- 20	mJ	
Single Pulse Avalanche Current	I <sub>AS</sub>	20	25		
Single Pulse Avalanche Energy	E <sub>AS</sub>	20	31.2	W	
Maximum Power Dissipation	P <sub>D</sub>	T <sub>C</sub> = 25 °C	3.25		3.25
		T <sub>C</sub> = 70 °C	2.10		2.10
		T <sub>A</sub> = 25 °C	2.0 <sup>b, c</sup>		2.0 <sup>b, c</sup>
		T <sub>A</sub> = 70 °C	1.25 <sup>b, c</sup>	1.25 <sup>b, c</sup>	
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS							
Parameter	Symbol	N-Channel		P-Channel		Unit	
		Typ	Max	Typ	Max		
Maximum Junction-to-Ambient <sup>b, d</sup>	t ≤ 10 s	R <sub>thJA</sub>	45	62.5	45	62.5	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R <sub>thJF</sub>	29	38	29	38	

Notes:

- Based on T<sub>C</sub> = 25 °C.
- Surface Mounted on 1" x 1" FR4 Board.
- t = 10 s.
- Maximum under Steady State conditions is 120 °C/W.

<b>SPECIFICATIONS</b> $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted							
Parameter	Symbol	Test Conditions	Min	Typ <sup>a</sup>	Max	Unit	
<b>Static</b>							
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	N-Ch	40		V	
		$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	P-Ch	-40			
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$	N-Ch		40	mV/ $^\circ\text{C}$	
		$I_D = -250\text{ }\mu\text{A}$	P-Ch		-40		
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	$I_D = 250\text{ }\mu\text{A}$	N-Ch		-4.8		
		$I_D = -250\text{ }\mu\text{A}$	P-Ch		4.0		
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	N-Ch	0.8		2.0	
		$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	P-Ch	-0.8		-2.2	
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 16\text{ V}$	N-Ch			100	
			P-Ch			-100	
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 40\text{ V}, V_{GS} = 0\text{ V}$	N-Ch			1	
		$V_{DS} = -40\text{ V}, V_{GS} = 0\text{ V}$	P-Ch			-1	
		$V_{DS} = 40\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$	N-Ch			10	
		$V_{DS} = -40\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$	P-Ch			-10	
On-State Drain Current <sup>b</sup>	$I_{D(on)}$	$V_{DS} = 5\text{ V}, V_{GS} = 10\text{ V}$	N-Ch	20		A	
		$V_{DS} = -5\text{ V}, V_{GS} = -10\text{ V}$	P-Ch	-20			
Drain-Source On-State Resistance <sup>b</sup>	$r_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 5\text{ A}$	N-Ch		0.013	0.016	
		$V_{GS} = -10\text{ V}, I_D = -5\text{ A}$	P-Ch		0.020	0.025	
		$V_{GS} = 4.5\text{ V}, I_D = 4\text{ A}$	N-Ch		0.015	0.019	
		$V_{GS} = -4.5\text{ V}, I_D = -4\text{ A}$	P-Ch		0.025	0.032	
Forward Transconductance <sup>b</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}, I_D = 5\text{ A}$	N-Ch		23	S	
		$V_{DS} = -15\text{ V}, I_D = -5\text{ A}$	P-Ch		18		
<b>Dynamic<sup>a</sup></b>							
Input Capacitance	$C_{iss}$	N-Channel $V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	N-Ch		2390	pF	
Output Capacitance	$C_{oss}$		P-Ch		2120		
Reverse Transfer Capacitance	$C_{rss}$	P-Channel $V_{DS} = -20\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	N-Ch		270		
			P-Ch		310		
Total Gate Charge	$Q_g$	$V_{DS} = 20\text{ V}, V_{GS} = 10\text{ V}, I_D = 5\text{ A}$	N-Ch		56	85	
		$V_{DS} = -20\text{ V}, V_{GS} = -10\text{ V}, I_D = -5\text{ A}$	P-Ch		52	80	
		N-Channel $V_{DS} = 20\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 5\text{ A}$	N-Ch		26	40	
			P-Ch		25.5	39	
Gate-Source Charge	$Q_{gs}$	P-Channel $V_{DS} = -20\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -5\text{ A}$	N-Ch		5.5	nC	
Gate-Drain Charge	$Q_{gd}$		P-Ch		5.1		
Gate Resistance	$R_g$	$f = 1\text{ MHz}$	N-Ch		2.6		4.0
			P-Ch		5.8		9.0



SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted							
Parameter	Symbol	Test Conditions	Min	Typ <sup>a</sup>	Max	Unit	
<b>Dynamic<sup>a</sup></b>							
Turn-On Delay Time	$t_{d(on)}$	N-Channel $V_{DD} = 20\text{ V}, R_L = 4\ \Omega$ $I_D \cong 5\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\ \Omega$  P-Channel $V_{DD} = -20\text{ V}, R_L = 4\ \Omega$ $I_D \cong -5\text{ A}, V_{GEN} = -10\text{ V}, R_g = 1\ \Omega$	N-Ch		15	23	ns
			P-Ch		13	20	
Rise Time	$t_r$		N-Ch		20	30	
			P-Ch		16	25	
Turn-Off Delay Time	$t_{d(off)}$		N-Ch		56	85	
			P-Ch		75	115	
Fall Time	$t_f$		N-Ch		10	15	
			P-Ch		68	105	
Turn-On Delay Time	$t_{d(on)}$	N-Ch		88	135		
		P-Ch		33	50		
Rise Time	$t_r$	N-Ch		117	180		
		P-Ch		93	140		
Turn-Off Delay Time	$t_{d(off)}$	N-Ch		62	95		
		P-Ch		80	120		
Fall Time	$t_f$	N-Ch		19	30		
		P-Ch		69	105		
<b>Drain-Source Body Diode Characteristics</b>							
Continuous Source-Drain Diode Current	$I_S$	$T_C = 25\text{ }^\circ\text{C}$	N-Ch			2.7	A
			P-Ch			-2.7	
Pulse Diode Forward Current <sup>a</sup>	$I_{SM}$		N-Ch			20	
			P-Ch			-20	
Body Diode Voltage	$V_{SD}$	$I_S = 1.5\text{ A}$	N-Ch		0.69	1.2	V
		$I_S = -1.6\text{ A}$	P-Ch		-0.72	-1.2	
Body Diode Reverse Recovery Time	$t_{rr}$	N-Channel $I_F = 2\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$  P-Channel $I_F = -2\text{ A}, di/dt = -100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$	N-Ch		62	95	ns
			P-Ch		49	75	
Body Diode Reverse Recovery Charge	$Q_{rr}$		N-Ch		62	95	nC
			P-Ch		42	65	
Reverse Recovery Fall Time	$t_a$		N-Ch		26		ns
			P-Ch		19		
Reverse Recovery Rise Time	$t_b$		N-Ch		36		
			P-Ch		30		

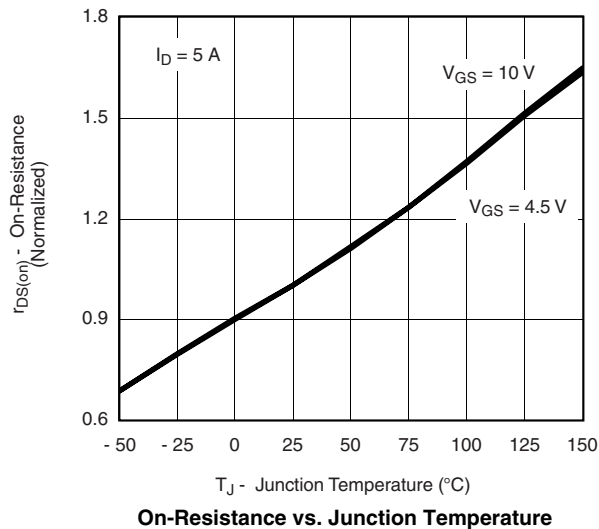
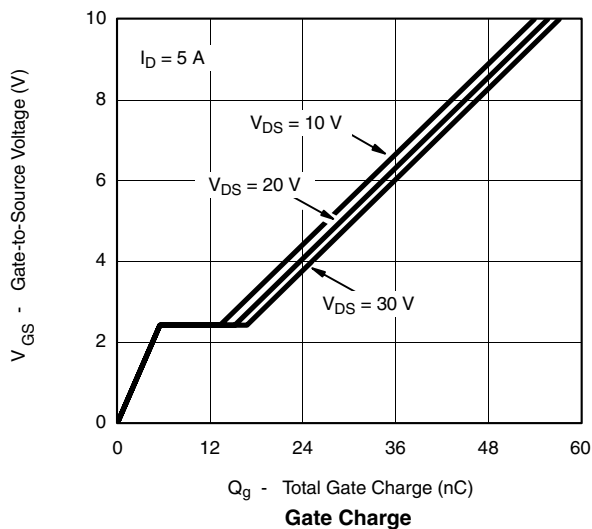
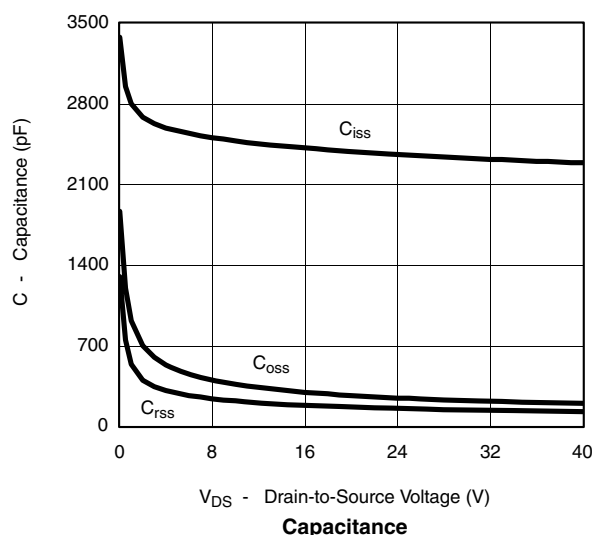
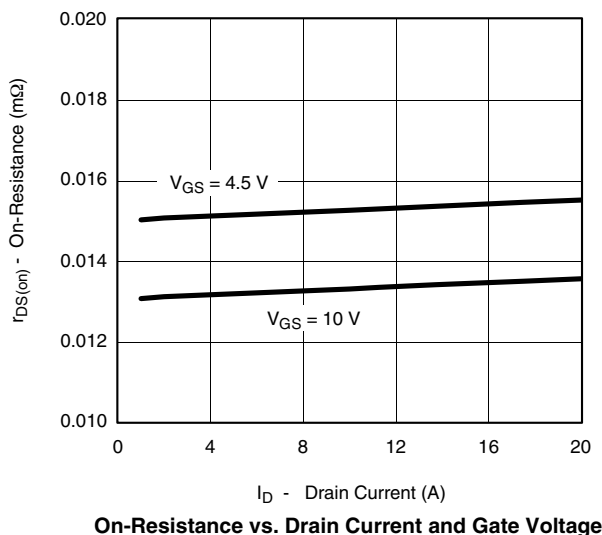
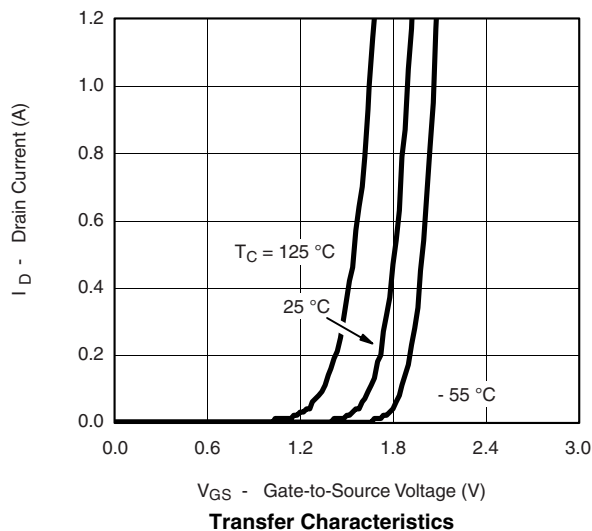
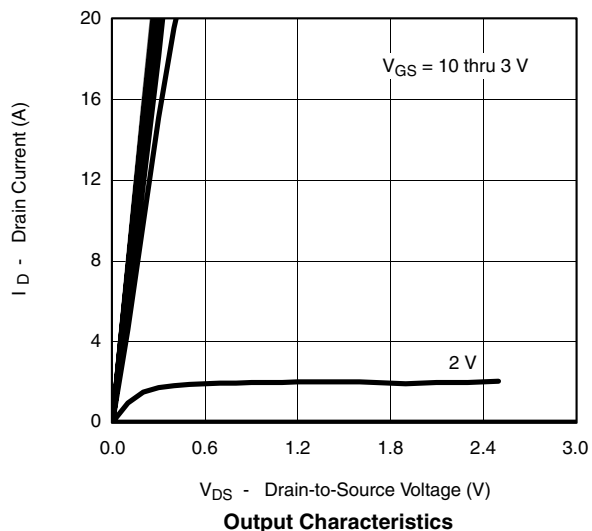
Notes:

- a. Guaranteed by design, not subject to production testing.
- b. Pulse test; pulse width  $\leq 300\ \mu\text{s}$ , duty cycle  $\leq 2\%$ .

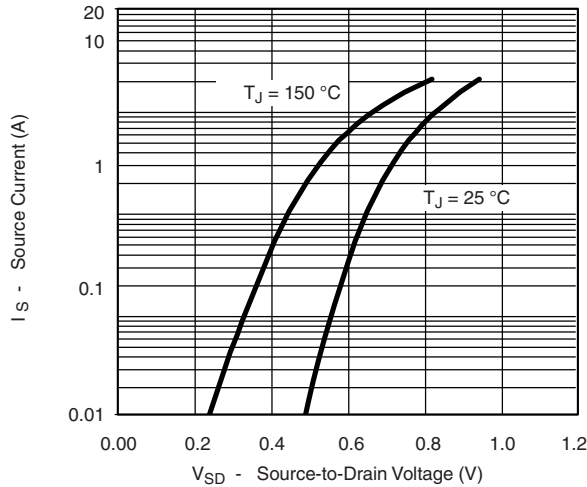
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



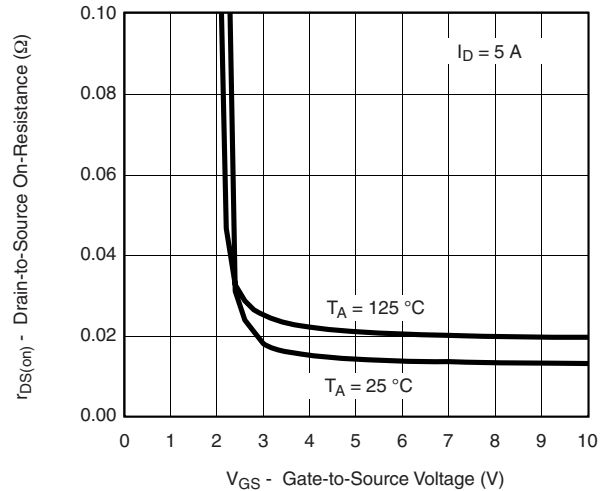
**N-CHANNEL TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



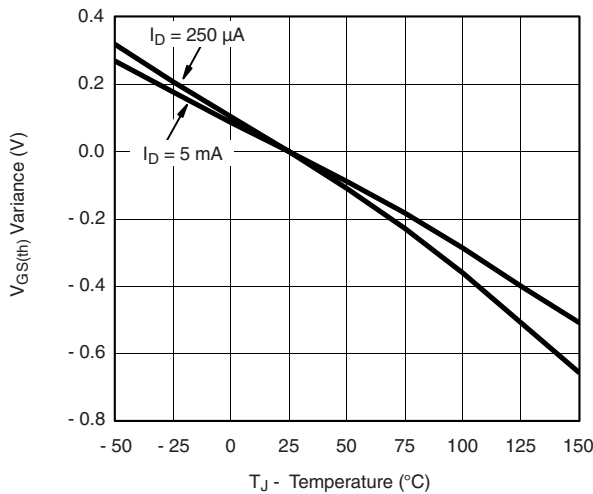
**N-CHANNEL TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



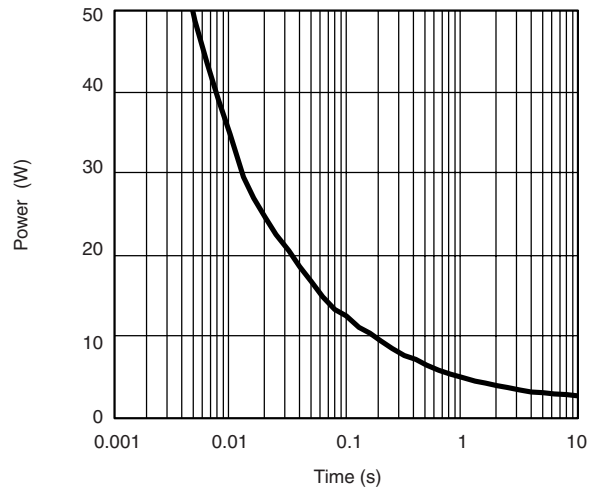
**Source-Drain Diode Forward Voltage**



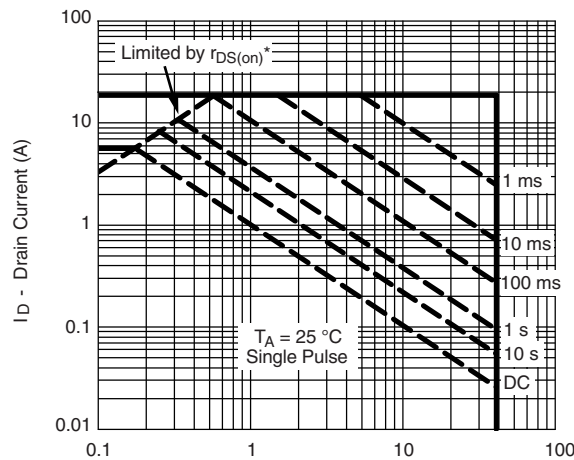
**On-Resistance vs. Gate-to-Source Voltage**



**Threshold Voltage**



**Single Pulse Power, Junction-to-Ambient**

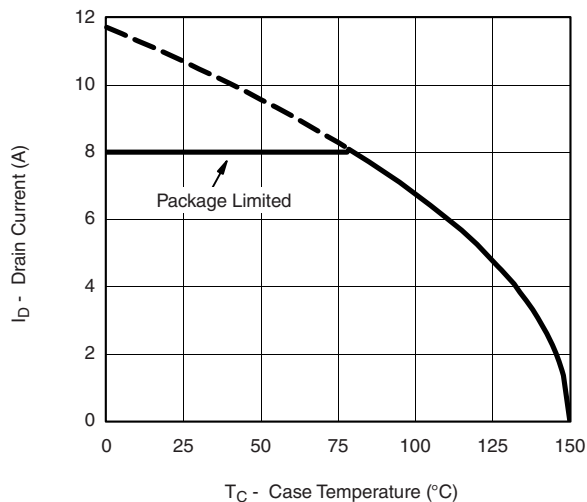


$V_{DS}$  - Drain-to-Source Voltage (V)  
\*  $V_{GS} >$  minimum  $V_{GS}$  at which  $r_{DS(on)}$  is specified

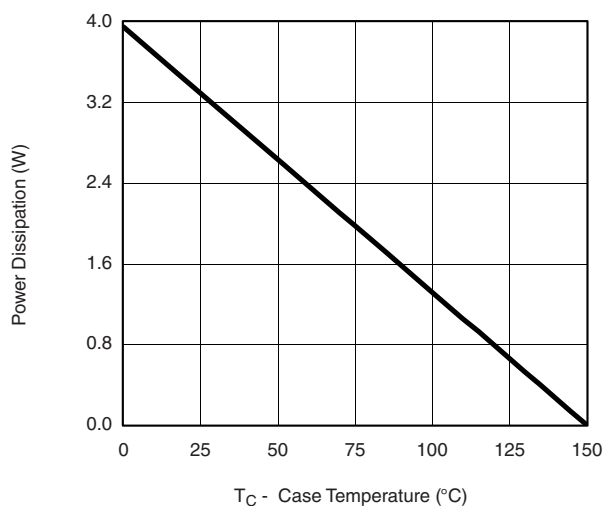
**Safe Operating Area, Junction-to-Ambient**



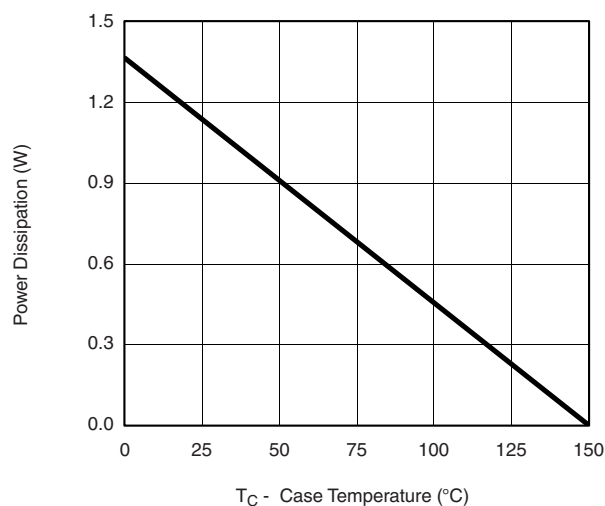
**N-CHANNEL TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



**Current Derating\***



**Power Derating, Junction-to-Foot**

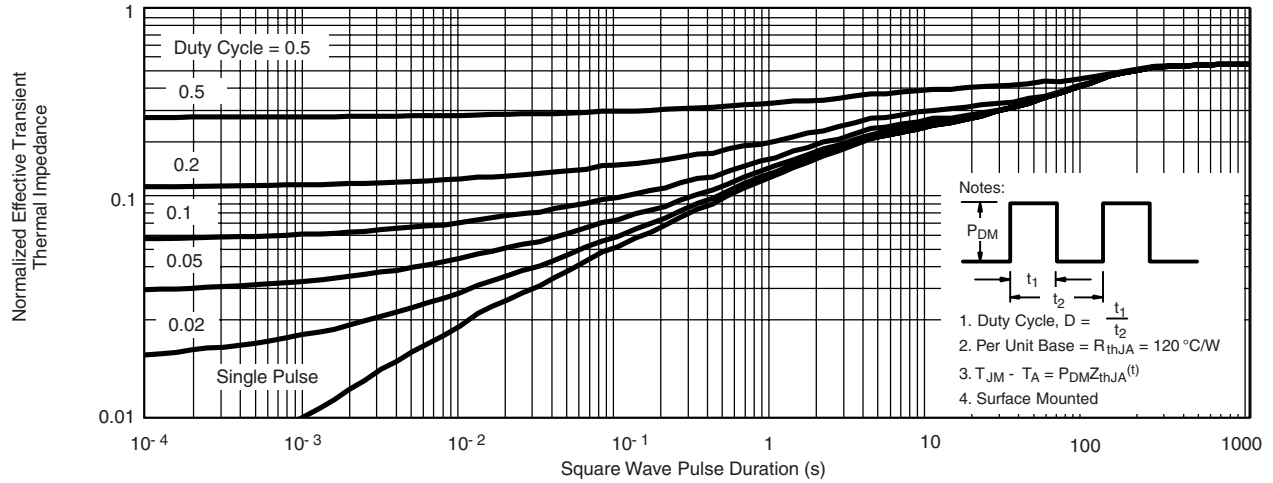


**Power Derating, Junction-to-Ambient**

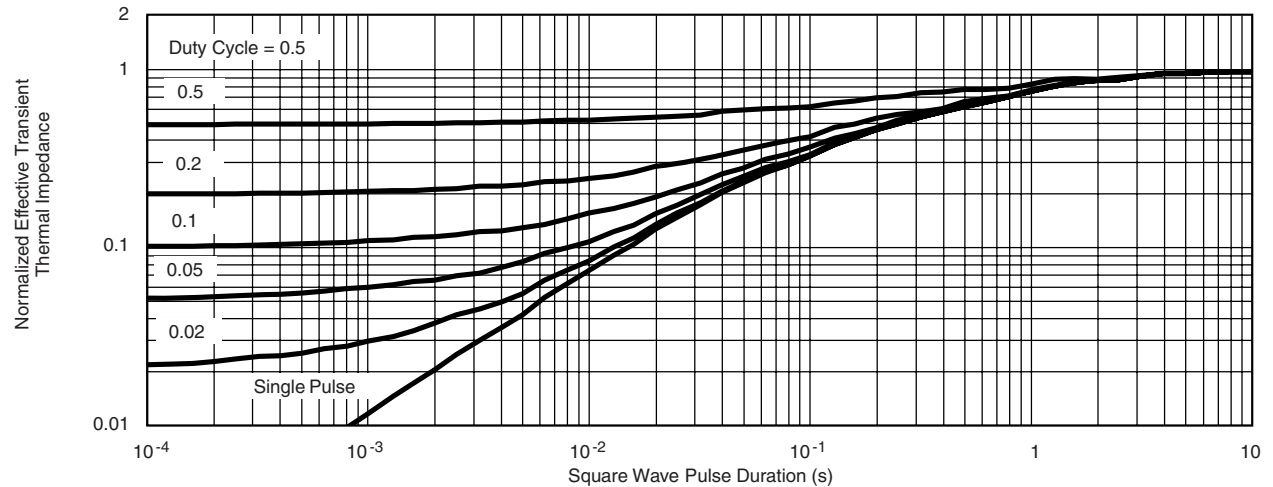
\* The power dissipation  $P_D$  is based on  $T_{J(max)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



**N-CHANNEL TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



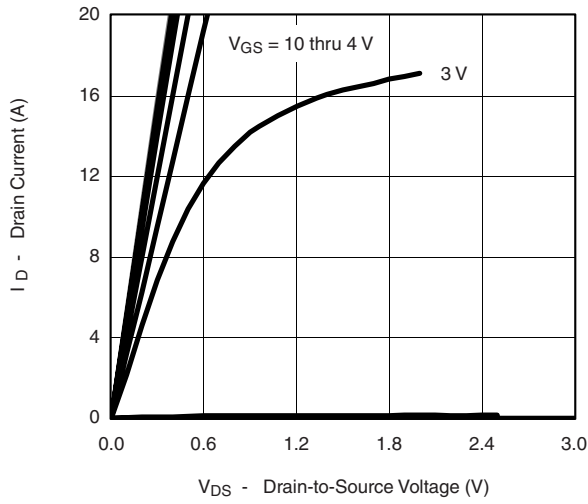
**Normalized Thermal Transient Impedance, Junction-to-Ambient**



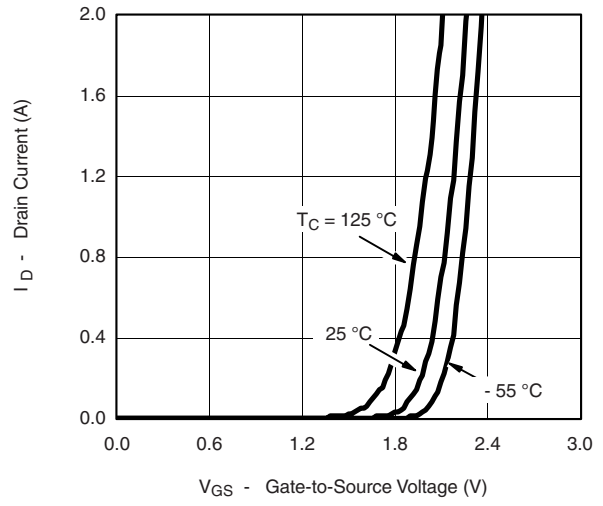
**Normalized Thermal Transient Impedance, Junction-to-Case**



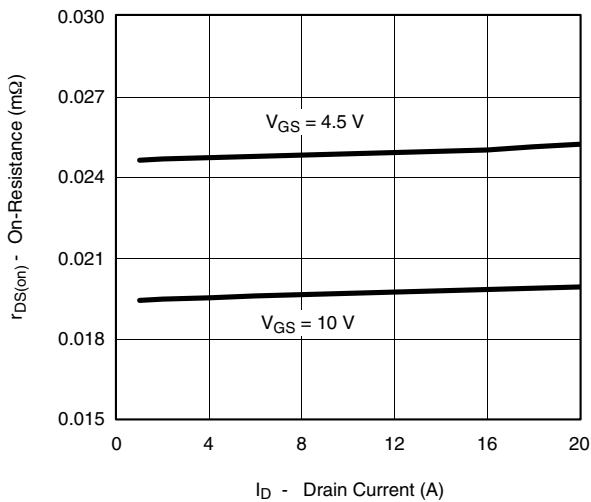
**P-CHANNEL TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



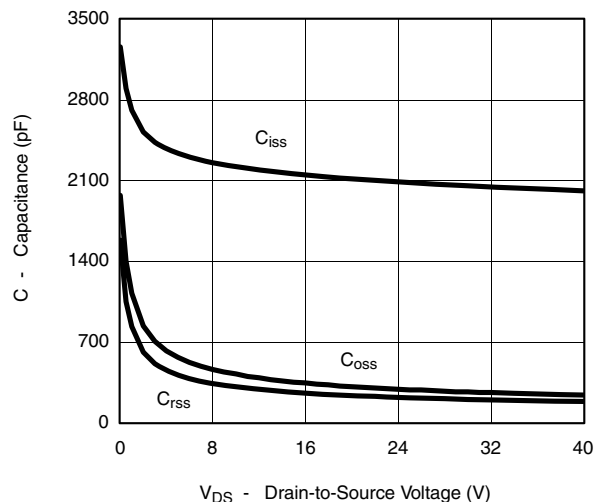
**Output Characteristics**



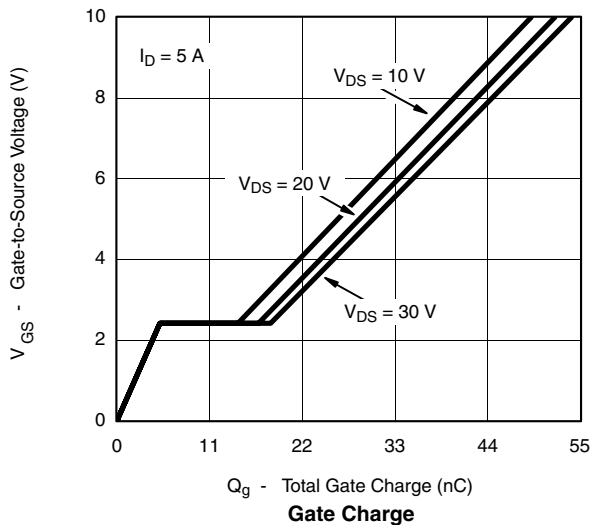
**Transfer Characteristics**



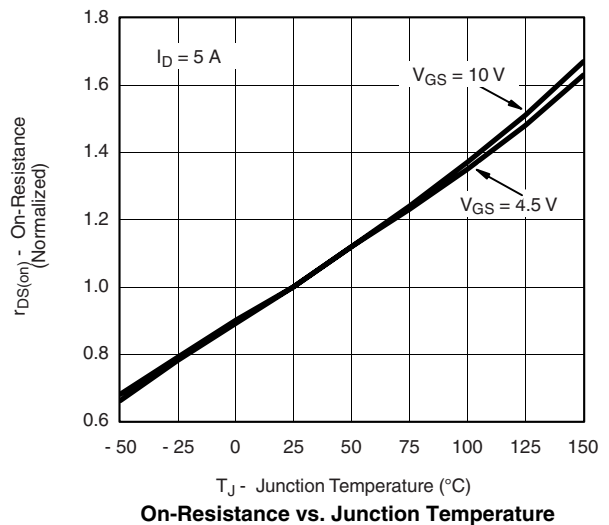
**On-Resistance vs. Drain Current and Gate Voltage**



**Capacitance**



**Gate Charge**

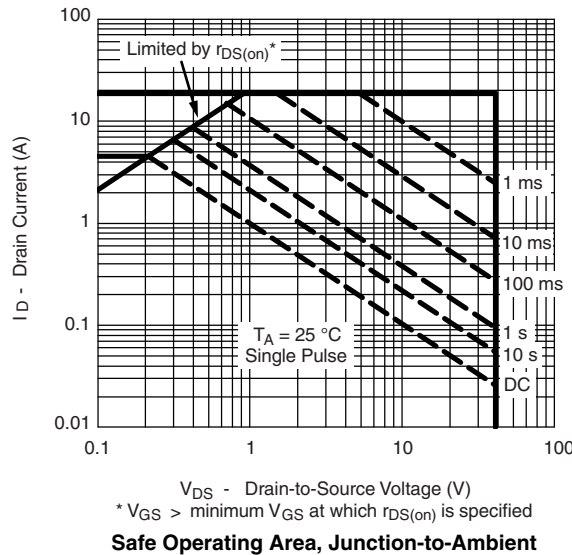
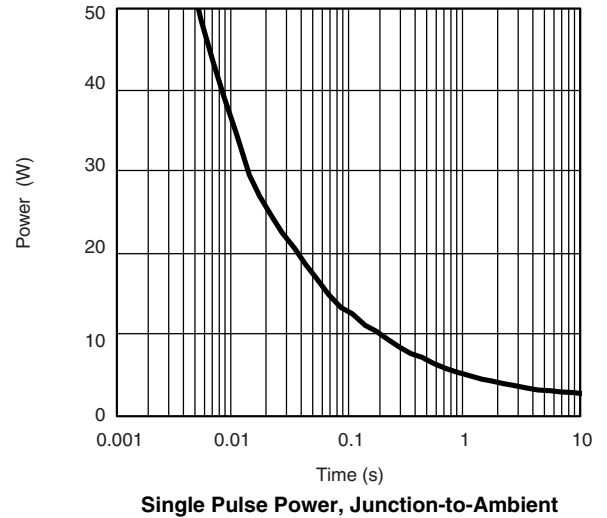
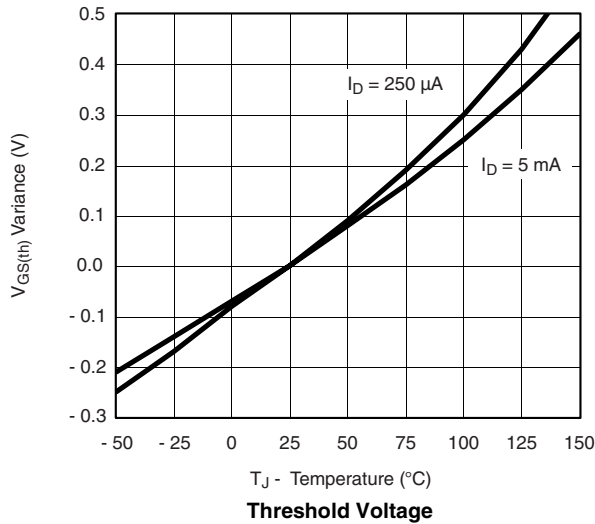
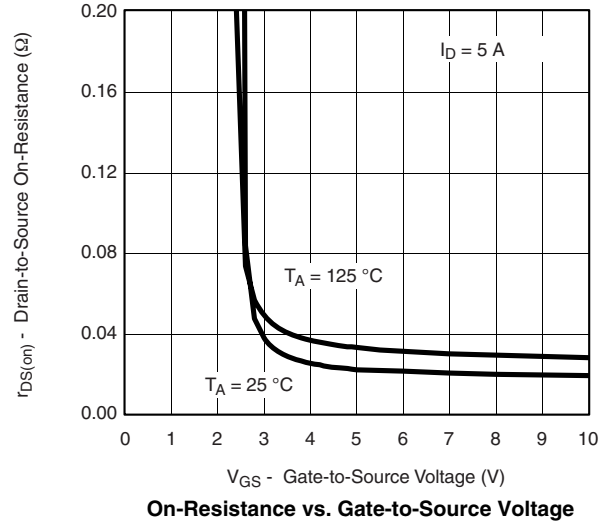
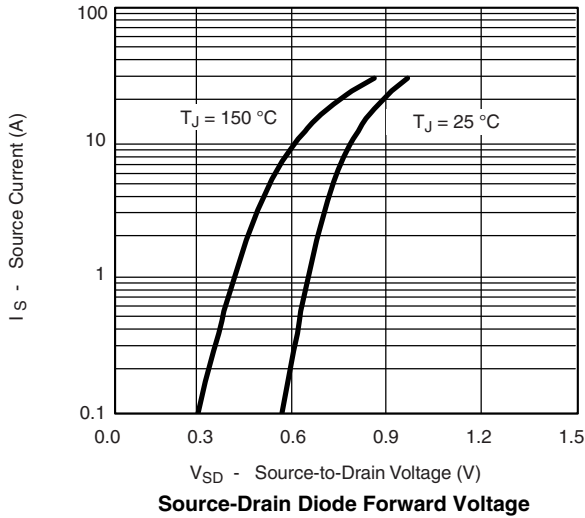


**On-Resistance vs. Junction Temperature**



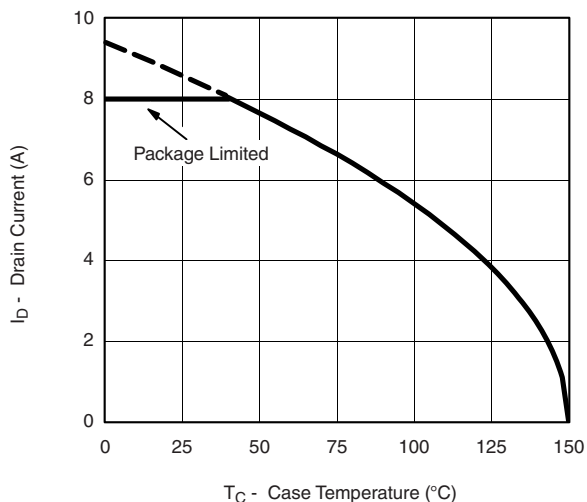


**P-CHANNEL TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



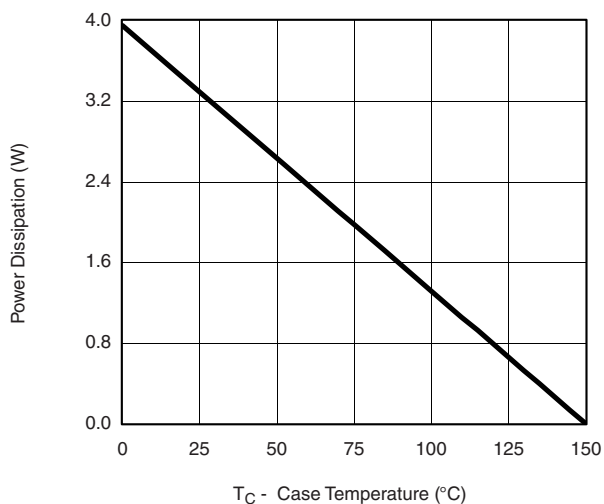


**P-CHANNEL TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



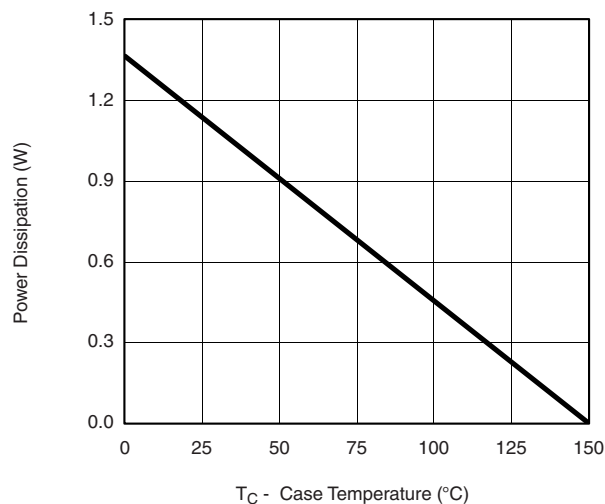
T<sub>C</sub> - Case Temperature (°C)

**Current Derating\***



T<sub>C</sub> - Case Temperature (°C)

**Power Derating, Junction-to-Foot**



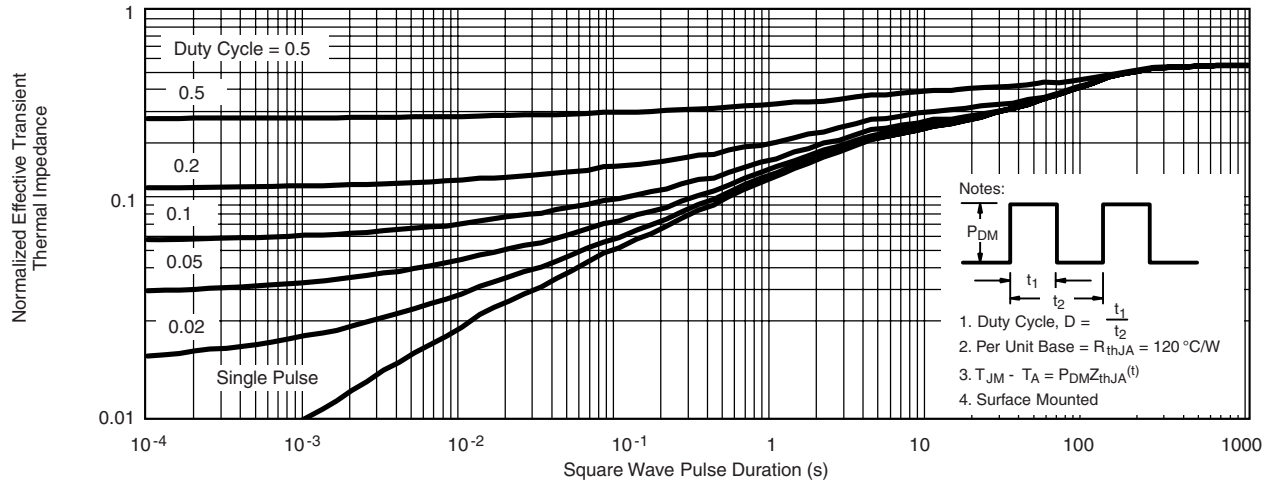
T<sub>C</sub> - Case Temperature (°C)

**Power Derating, Junction-to-Ambient**

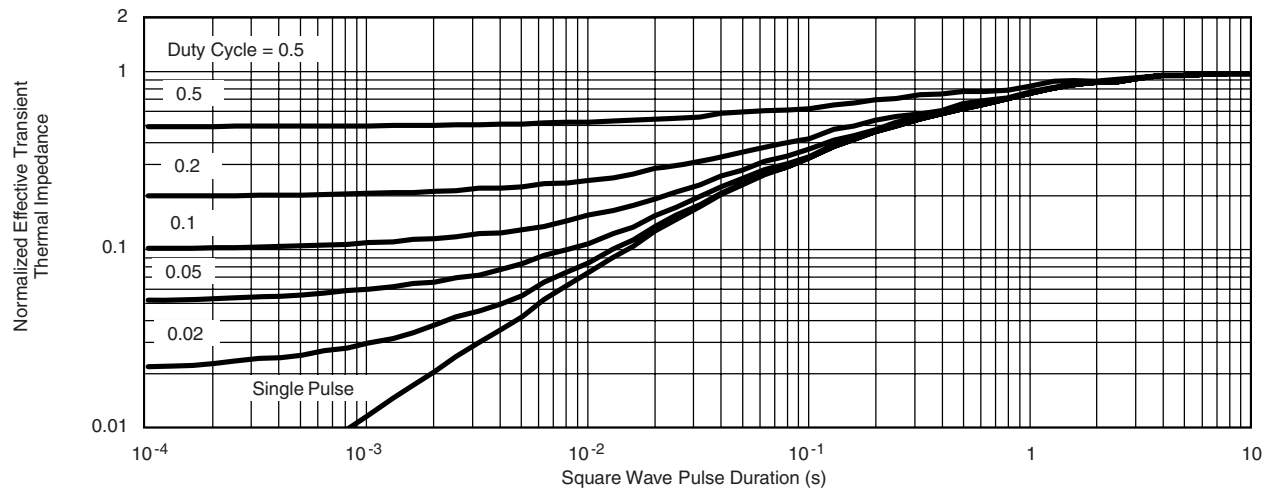
\* The power dissipation P<sub>D</sub> is based on T<sub>J(max)</sub> = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



**P-CHANNEL TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



**Normalized Thermal Transient Impedance, Junction-to-Ambient**



**Normalized Thermal Transient Impedance, Junction-to-Case**

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